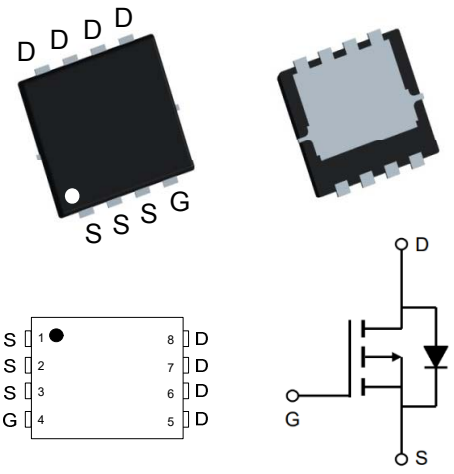
LOW VOLTAGE MOSFET (P-CHANNEL)

FEATURES

- V_{DS}=-30V,$R_{DS(ON)}$≤10mΩ @V_{GS}=-10V,I_D=-10A
- Ultra Low on-resistance
- For Low power DC to DC converter application
- For Load switch application
- Surface Mount device



PDFN3333

MECHANICAL DATA

- Case: PDFN3333
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.012 grams (approximate)
- Marking:Q30P03

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current[1]	-60	A
I_D@T_C=100°C	Continuous Drain Current[1]	-30	A
I_{DM}	Pulsed Drain Current[2]	-90	A
EAS	Single Pulse Avalanche Energy[3]	64	mJ
I_{AS}	Avalanche Current	30	A
P_D@T_C=25°C	Total Power Dissipation[4]	32	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	-30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10 V , I_D=10A		7.4	10	mΩ
		V_{GS}=4.5V , I_D=10A		11.4	13.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	-1.0	-1.6	-2.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25°C	---	---	-1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=125°C	---	---	-10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
Rg	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.8	----	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=15V , V_{GS}=10V , I_D=20A	---	81	---	nC
Q_{gs}	Gate-Source Charge		---	12	---	
Q_{gd}	Gate-Drain Charge		---	9.7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3Ω, I_D=15A	---	17	---	ns
T_r	Rise Time		---	21	---	
$T_{d(off)}$	Turn-Off Delay Time		---	36	---	
T_f	Fall Time		---	15	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	3980	---	pF
C_{oss}	Output Capacitance		---	450	---	
C_{rss}	Reverse Transfer Capacitance		---	420	---	

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Typical Characteristics

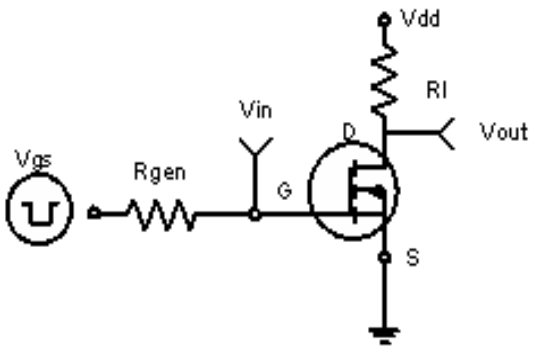


Figure 1 Switching Test Circuit

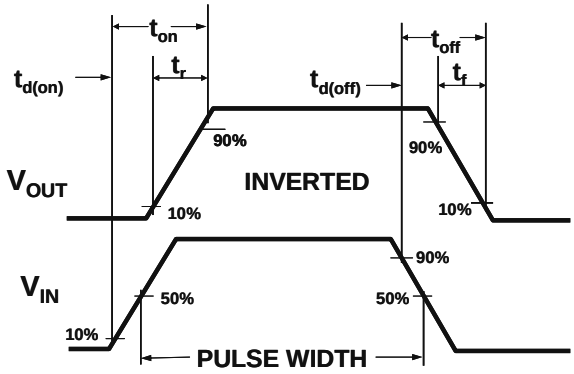
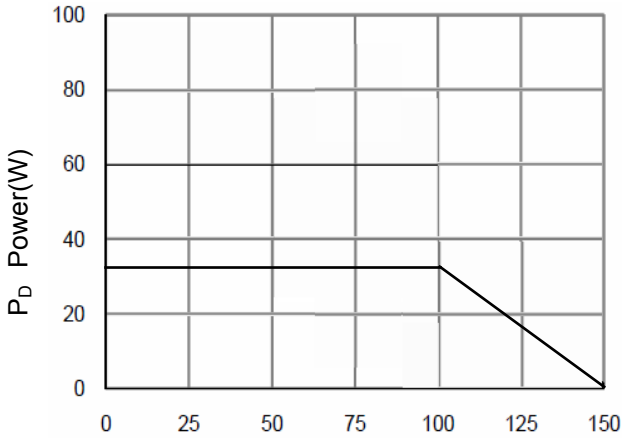
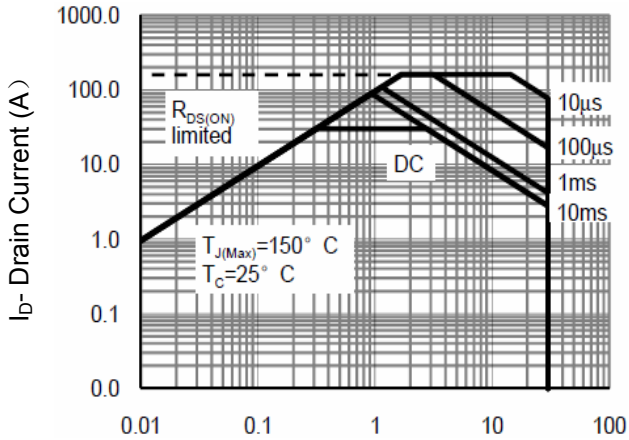


Figure 2 Switching Waveforms



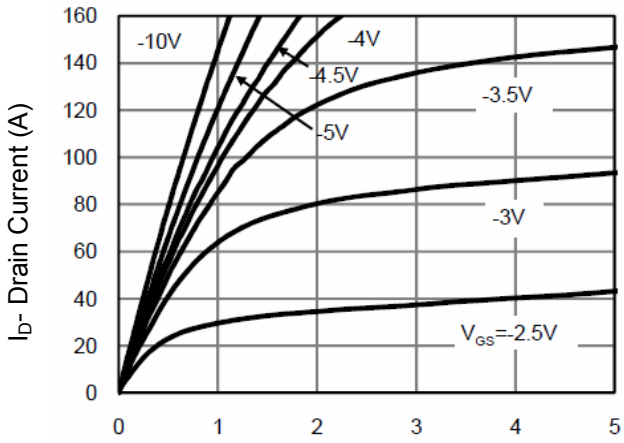
TJ-Junction Temperature(℃)

Figure 3 Power Dissipation



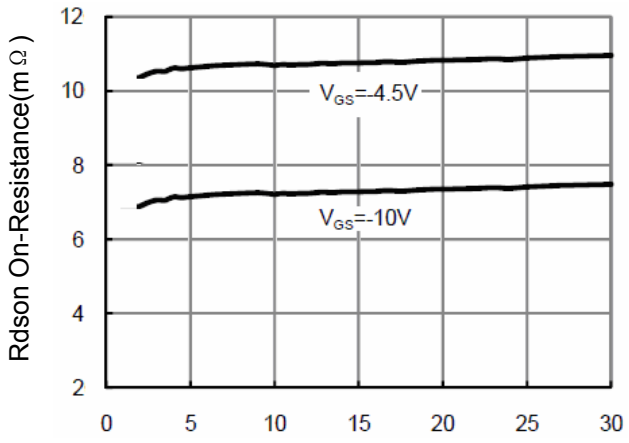
Vds Drain-Source Voltage (V)

Figure 4 Safe Operation Area



Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics



ID- Drain Current (A)

Figure 6 Drain-Source On-Resistance

LOW VOLTAGE MOSFET (P-CHANNEL)

Typical Characteristics

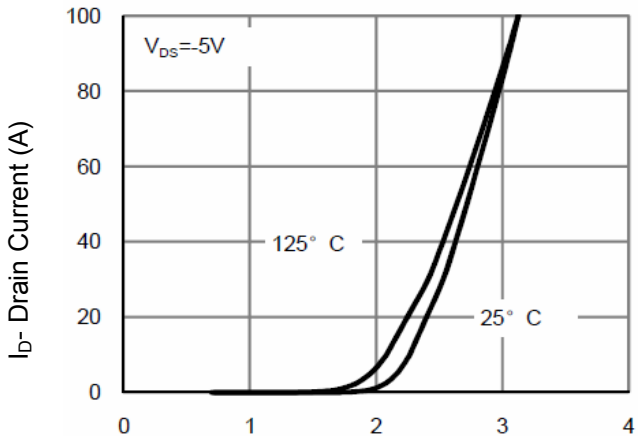


Figure 7 Transfer Characteristics

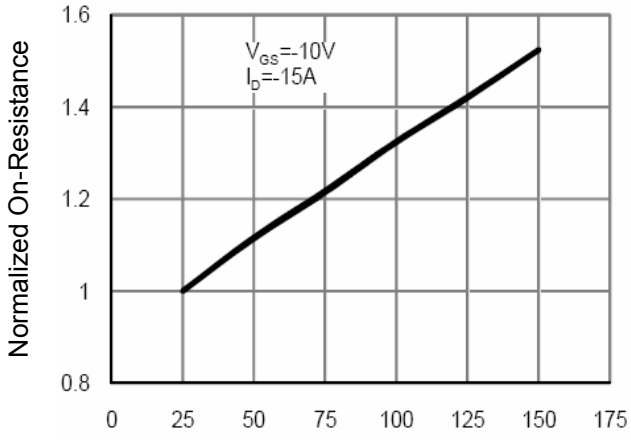


Figure 8 Drain-Source On-Resistance

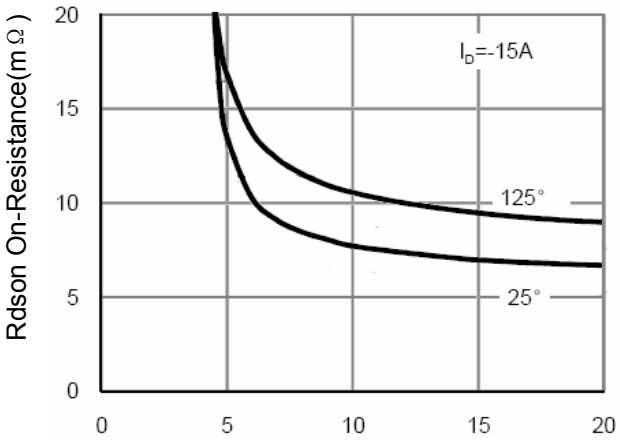


Figure 9 Rdson vs Vgs

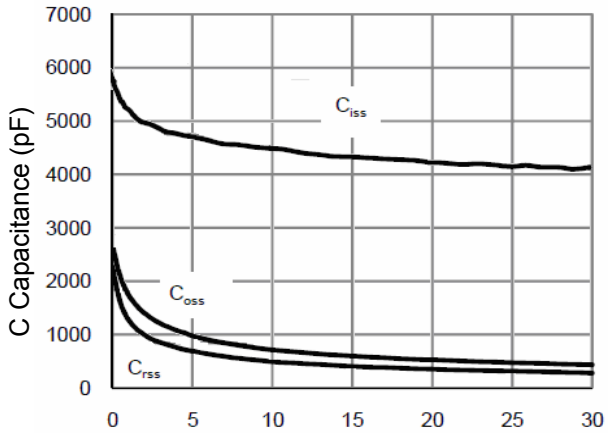


Figure 10 Capacitance vs Vds

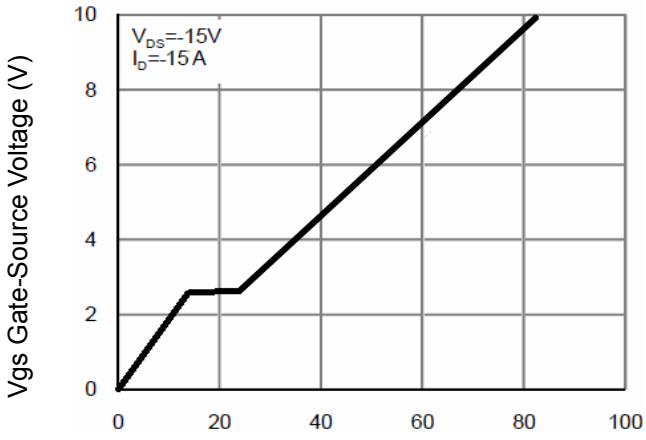


Figure 11 Gate Charge

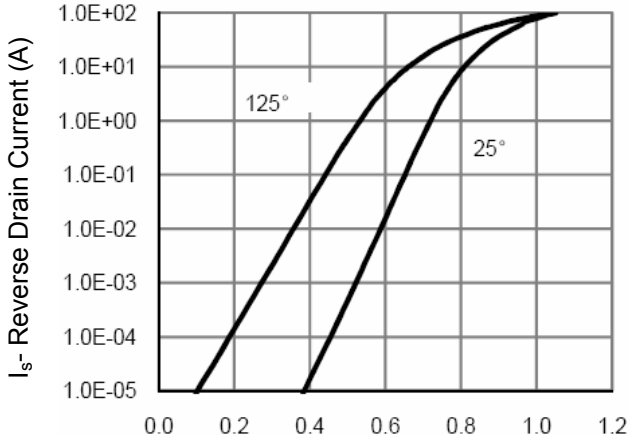


Figure 12 Source- Drain Diode Forward

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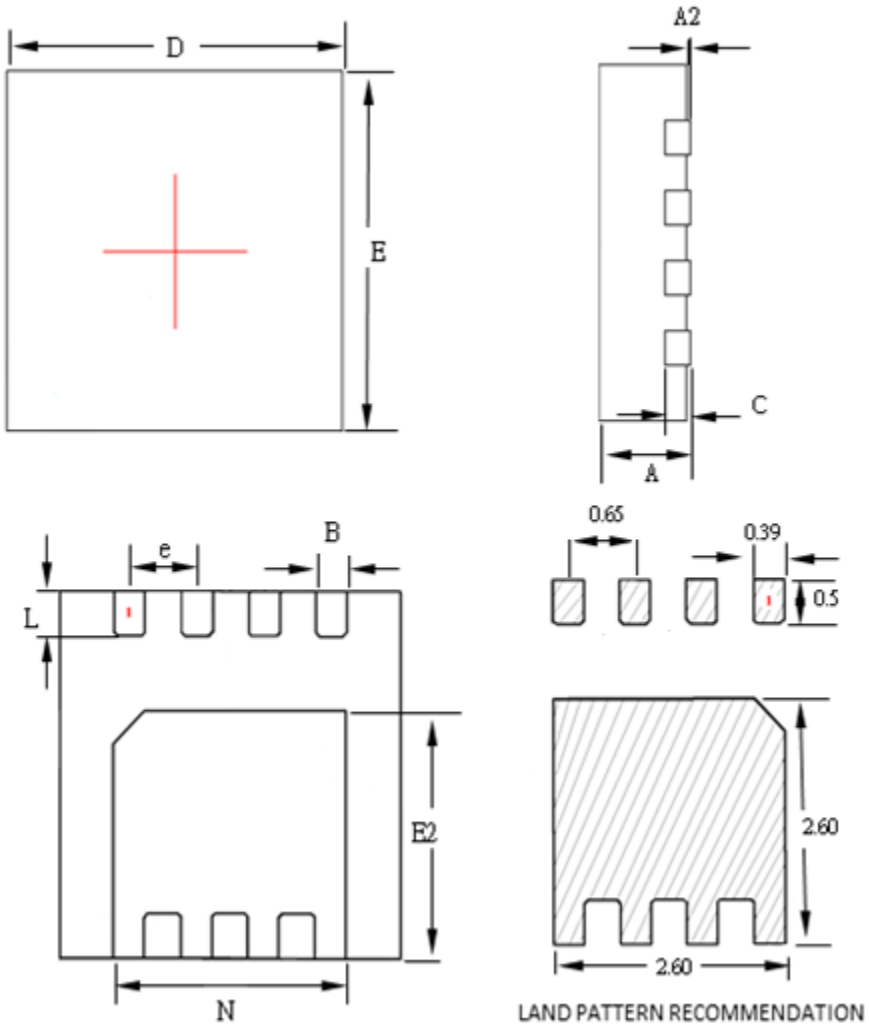

SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A2	0.00	--	0.05	0.000	--	0.002
B	0.24	0.30	0.35	0.009	0.012	0.014
C	0.10	0.15	0.25	0.004	0.006	0.010
D	3.15	3.30	3.40	0.124	0.130	0.134
E	3.15	3.30	3.40	0.124	0.130	0.134
E2	2.15	2.25	2.35	0.085	0.089	0.093
L	0.35	0.40	0.45	0.014	0.016	0.018
N	2.10	2.25	2.35	0.083	0.089	0.093
e	--	0.65	--	--	0.026	--